

## IN THE CLAIMS

Please amend Claim 1, to read as follows.

1. (Currently Amended) A method for making a through-hole in a silicon substrate comprising the steps of:

forming a high-impurity-concentration region ~~in the periphery of a through-hole-forming region~~ at a first surface of the silicon substrate so as to surround a through-hole-forming region;

forming an etching stop layer over the through-hole-forming region and the high-impurity-concentration region;

forming a mask layer having an opening on a second surface of the silicon substrate, the second surface being opposite to the first surface;

etching the silicon substrate at the opening through the mask layer until the etching stop layer is exposed to the second surface;

further etching the silicon substrate until the etched portion extends to the high-impurity-concentration region; and

removing the etching stop layer at least at the portion exposed to the second surface.

2. (Original) A method for making a through-hole according to Claim 1, wherein the high-impurity-concentration region has an impurity concentration of  $1 \times 10^{19}/\text{cm}^3$  or more.

3. (Original) A method for making a through-hole according to Claim 2, wherein the high-impurity-concentration region has an impurity concentration of  $7 \times 10^{19} \text{ cm}^{-3}$  or more.

4. (Original) A method for making a through-hole according to Claim 1, wherein the impurity is selected from the group consisting of boron, phosphorus, arsenic, and antimony.

5. (Original) A method for making a through-hole according to Claim 1, wherein the high-impurity-concentration region has a width of 1 to 20  $\mu\text{m}$  and a depth of 1 to 3  $\mu\text{m}$ .

6. (Original) A method for making a through-hole according to Claim 1, wherein the high-impurity-concentration region is formed by forming an impurity diffusion layer in the first surface of the silicon substrate.

7. (Original) A method for making a through-hole according to Claim 1, wherein the etching stop layer comprises a silicon nitride film formed by low-pressure vapor deposition (LP-SiN).

8. (Withdrawn) An ink-jet printer head comprising an ink supply port fabricated by a method for making a through-hole according to any one of Claims 1 to 7.